

Low Voltage, Low On-Resistance, Dual DPDT/Quad SPDT Analog Switch

DESCRIPTION

The DG2788/DG2789 are monolithic CMOS analog switching products designed for high performance switching of analog signals. Combining low power, high speed, low on-resistance and small physical size, the DG2788/DG2789 are ideal for portable and battery powered applications requiring high performance and efficient use of board space.

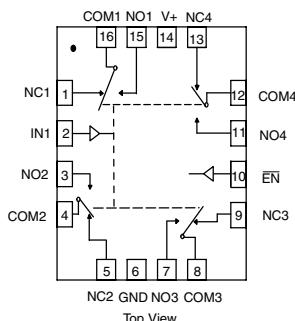
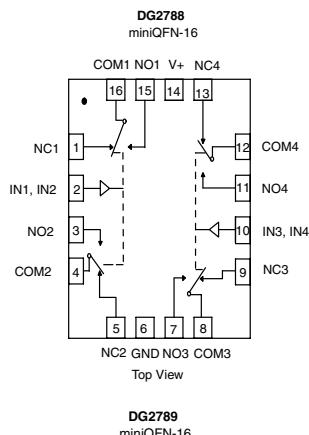
The DG2788/DG2789 are built on Vishay Siliconix's low voltage process. An epitaxial layer prevents latchup. Break-before-make is guaranteed.

The switch conducts equally well in both directions when on, and blocks up to the power supply level when off. The DG2788 is configured as a dual Double Pole Double Throw switches while the DG2789 is configured as a Quad Single Pole Double Throw. The DG2789 has one control pin for all four SPDT switches and also has an enable pin that can turn all switches off.

The DG2788 and DG2789 comes in a small miniQFN-16 lead package (2.6 x 1.8 x 0.75 mm).

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations and is 100 % RoHS compliant.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



FEATURES

- Low Voltage Operation (1.65 V to 4.3 V)
- Low On-Resistance - r_{ON} : 0.4 Ω Typ. at 2.7 V
- Fast Switching: $t_{ON} = 47$ ns
 $t_{OFF} = 15$ ns
- miniQFN-16 Package
- Latch-Up Current > 300 mA (JESD78)



BENEFITS

- Reduced Power Consumption
- High Accuracy
- Reduce Board Space
- TTL/1.8 V Logic Compatible
- High Bandwidth

APPLICATIONS

- Cellular Phones
- Speaker Headset Switching
- Audio and Video Signal Routing
- PCMCIA Cards
- Battery Operated Systems

TRUTH TABLE DG2788

Logic	NC1, 2, 3 and 4	NO1, 2, 3 and 4
0	ON	OFF
1	OFF	ON

TRUTH TABLE DG2789

EN Logic	IN Logic	NC1, 2, 3 and 4	NO1, 2, 3 and 4
0	0	ON	OFF
0	1	OFF	ON
1	x	OFF	OFF

ORDERING INFORMATION

Temp Range	Package	Part Number
- 40 to 85 °C	miniQFN-16	DG2788DTN-T1-E4 DG2789DTN-T1-E4

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	Limit	Unit
Reference to GND	V+		- 0.3 to 5.0	V
	IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	
Current (Any terminal except NO, NC or COM)			30	mA
Continuous Current (NO, NC, or COM)			± 300	
Peak Current (Pulsed at 1 ms, 10 % duty cycle)			± 500	
Storage Temperature (D Suffix)			- 65 to 150	°C
Package Solder Reflow Conditions ^d	miniQFN-16		250	
Power Dissipation (Packages) ^b	miniQFN-16 ^c		525	mW

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 6.6 mW/°C above 70 °C
- d. Manual soldering with iron is not recommended for leadless components. The miniQFN-16 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

SPECIFICATIONS ($V_+ = 3\text{ V}$)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified $V_+ = 3\text{ V}, \pm 10\%, V_{IN} = 0.5\text{ or }1.4\text{ V}^e$	Temp ^a	Limits			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V_+	V
On-Resistance	r_{ON}	$V_+ = 2.7\text{ V}, V_{COM} = 0.5\text{ V}, I_{NO}, I_{NC} = 100\text{ mA}$	Room		0.4	0.5	Ω
		$V_+ = 2.7\text{ V}, V_{COM} = 1.5\text{ V}, I_{NO}, I_{NC} = 100\text{ mA}$			0.33		
			Full			0.56	
r_{ON} Flatness ^d	r_{ON} Flatness	$V_+ = 2.7\text{ V}, V_{COM} = 0\text{ to }V_+, I_{NO}, I_{NC} = 100\text{ mA}$	Room		0.1	0.15	
r_{ON} Match ^d	Δr_{ON}		Room		0.05		
Switch Off Leakage Current	$I_{NO(off)}, I_{NC(offF)}$	$V_+ = 3.3\text{ V}, V_{NO}, V_{NC} = 0.3\text{ V}/3.0\text{ V}, V_{COM} = 3.0\text{ V}/0.3\text{ V}$	Room	- 1		1	nA
	$I_{COM(off)}$		Full	- 10		10	
Channel-On Leakage Current	$I_{COM(on)}$	$V_+ = 3.3\text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3\text{ V}/3.0\text{ V}$	Room	- 1		1	
			Full	- 10		10	
Digital Control							
Input High Voltage	V_{INH}		Full	1.4			V
Input Low Voltage	V_{INL}		Full			0.5	
Input Capacitance	C_{in}		Full		6		
Input Current	I_{INL} or I_{INH}	$V_{IN} = 0\text{ or }V_+$	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time	t_{ON}	$V_{NO} \text{ or } V_{NC} = 1.5\text{ V}, R_L = 50\text{ }\Omega, C_L = 35\text{ pF}$	Room		47	72	ns
Turn-Off Time	t_{OFF}		Full		75		
Break-Before-Make Time	t_d		Room		15	43	
Charge Injection ^d	Q_{INJ}	$C_L = 1\text{ nF}, V_{GEN} = 0\text{ V}, R_{GEN} = 0\text{ }\Omega$	Full	1		45	
Off-Isolation ^d	OIRR	$R_L = 50\text{ }\Omega, C_L = 5\text{ pF}, f = 100\text{ kHz}$	Room		- 69		dB
		$R_L = 50\text{ }\Omega, C_L = 5\text{ pF}, f = 1\text{ MHz}$			- 49		
Crosstalk ^{d, f}	X_{TALK}	$R_L = 50\text{ }\Omega, C_L = 5\text{ pF}, f = 100\text{ kHz}$			- 106		
		$R_L = 50\text{ }\Omega, C_L = 5\text{ pF}, f = 1\text{ MHz}$			- 96		
N_O, N_C Off Capacitance ^d	$C_{NO(off)}$	$f = 1\text{ MHz}$	Room		81		pF
	$C_{NC(off)}$		Room		81		
Channel-On Capacitance ^d	$C_{NO(on)}$		Room		186		
	$C_{NC(on)}$		Room		186		
Power Supply							
Power Supply Range	V_+			2.7		3.3	V
Power Supply Current	I_+	$V_{IN} = 0\text{ or }V_+$	Full			1.0	μA

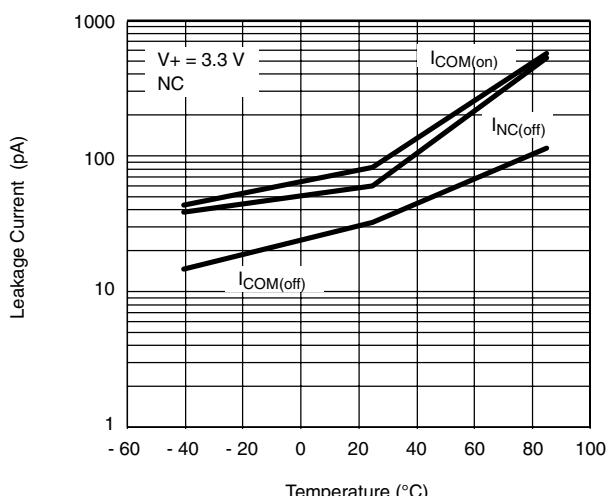
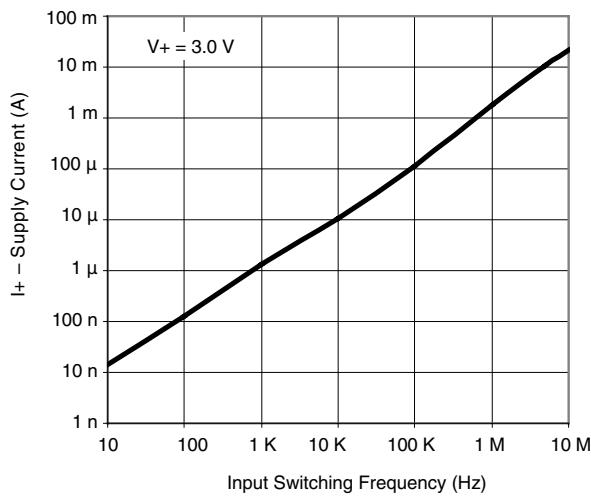
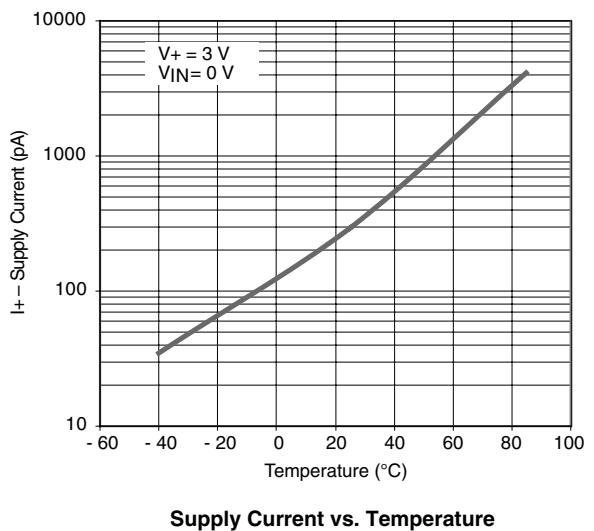
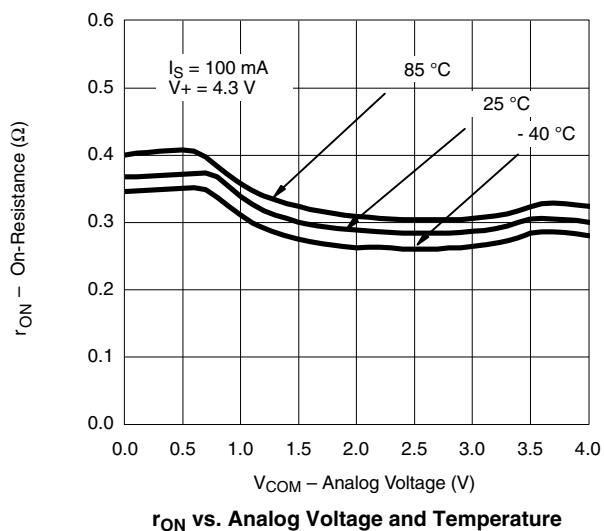
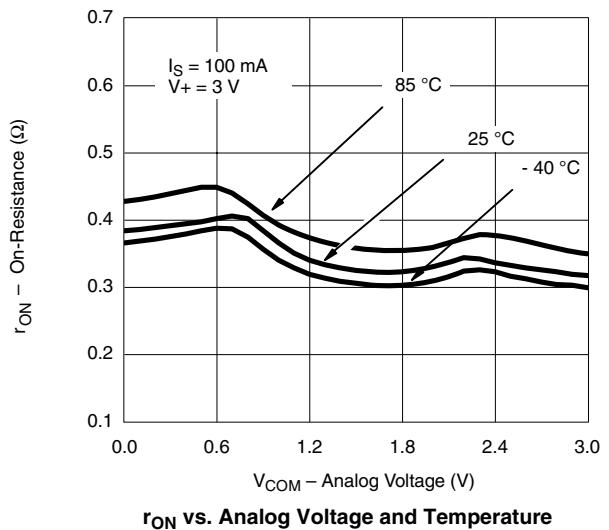
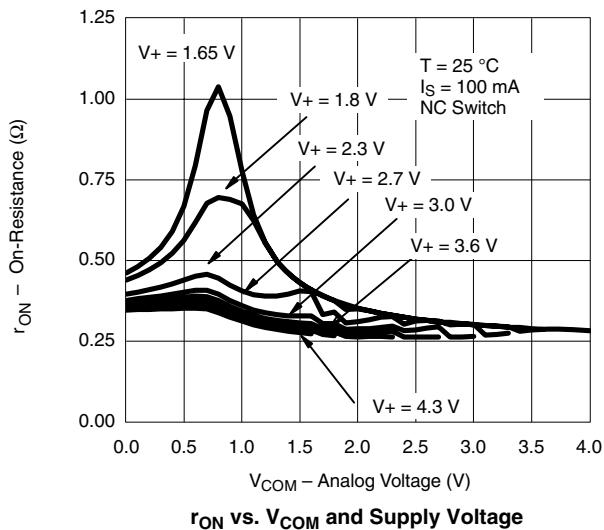
SPECIFICATIONS (V₊ = 4.3 V)

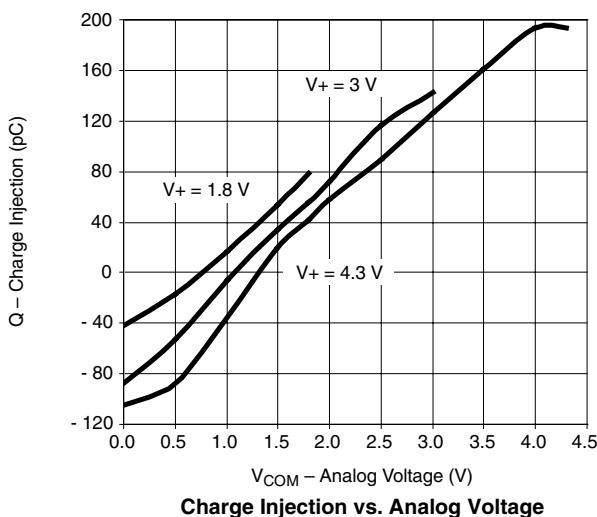
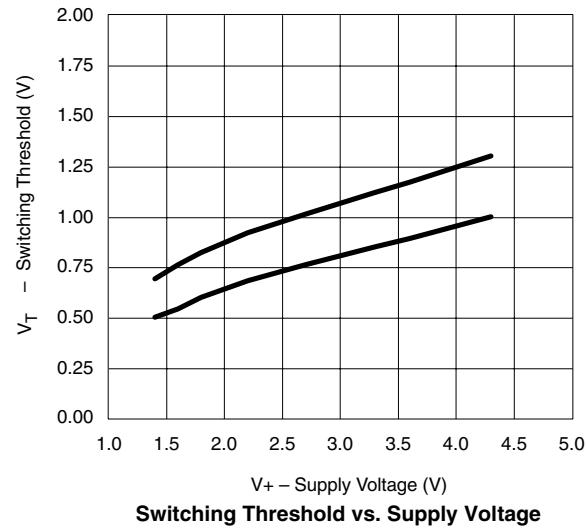
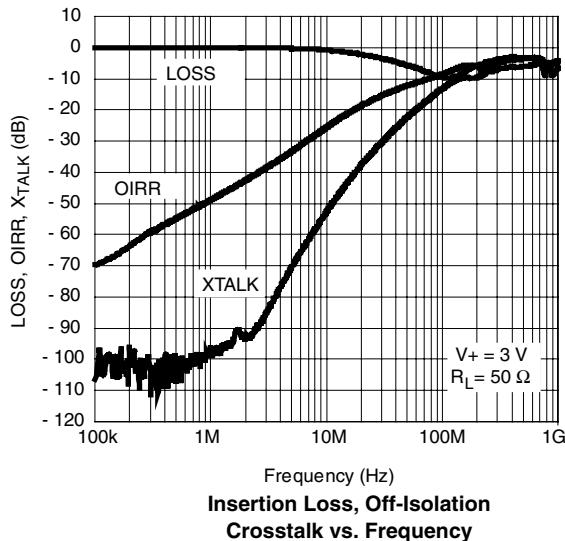
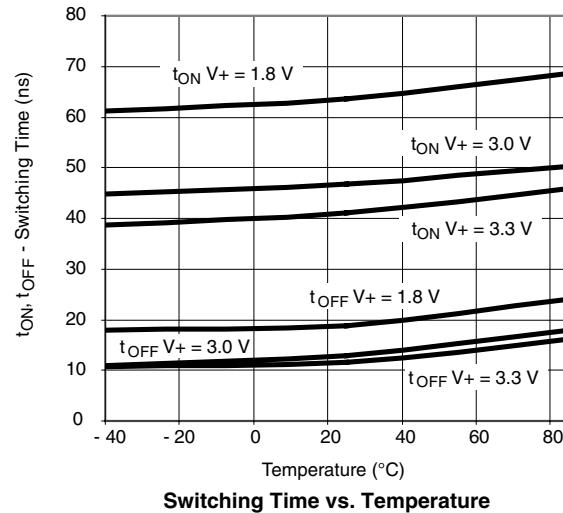
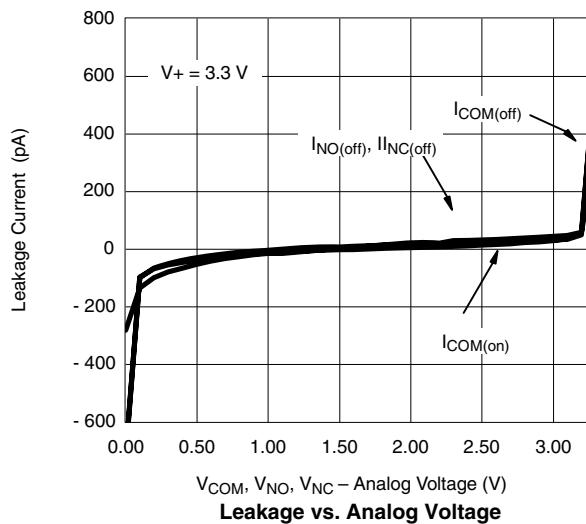
Parameter	Symbol	Test Conditions Otherwise Unless Specified V ₊ = 4.3 V, V _{IN} = 0.5 or 1.6 V ^e	Temp ^a	Limits			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V ₊	V
On-Resistance	r _{ON}	V ₊ = 4.3 V, V _{COM} = 0.9 V, I _{NO} , I _{NC} = 100 mA	Room		0.32	0.45	Ω
		V ₊ = 4.3 V, V _{COM} = 2.5 V, I _{NO} , I _{NC} = 100 mA			0.27		
			Full			0.5	
r _{ON} Flatness ^d	r _{ON} Flatness	V ₊ = 4.3 V, V _{COM} = 0 to V ₊ , I _{NO} , I _{NC} = 100 mA	Room		0.1	0.15	nA
r _{ON} Match ^d	Δr _{ON}		Room		0.03		
Switch Off Leakage Current ^d	I _{NO(off)} , I _{NC(offF)}	V ₊ = 4.3 V, V _{NO} , V _{NC} = 0.3 V / 4.0 V, V _{COM} = 4.0 V / 0.3 V	Room Full	-10 - 100		10 100	
	I _{COM(off)}		Room Full	- 10 - 100		10 100	
Channel-On Leakage Current ^d	I _{COM(on)}	V ₊ = 4.3 V, V _{NO} , V _{NC} = V _{COM} = 3.0 V / 4.0 V	Room Full	- 10 - 100		10 100	
Digital Control							
Input High Voltage	V _{INH}		Full	1.6			V
Input Low Voltage	V _{INL}		Full			0.5	
Input Capacitance	C _{in}		Full		6		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V ₊	Full	- 1		1	μA
Dynamic Characteristics							
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω	Room		105		pC
N _O , N _C Off Capacitance ^d	C _{NO(off)}	f = 1 MHz	Room		79		pF
	C _{NC(off)}		Room		79		
Channel-On Capacitance ^d	C _{NO(on)}		Room		183		
	C _{NC(on)}		Room		183		
Power Supply							
Power Supply Range	V ₊					4.3	V
Power Supply Current	I ₊	V _{IN} = 0 or V ₊	Full			1.0	μA

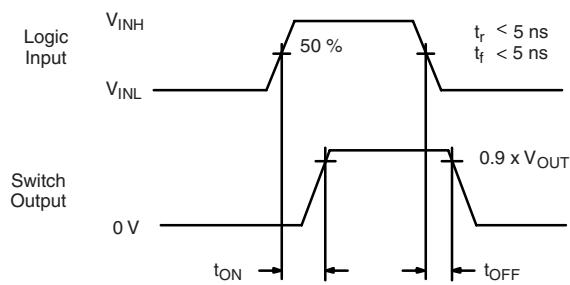
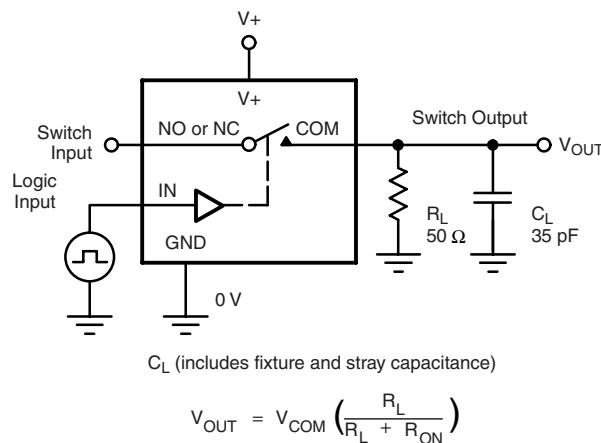
Notes:

- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, not subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Crosstalk measured between channels.

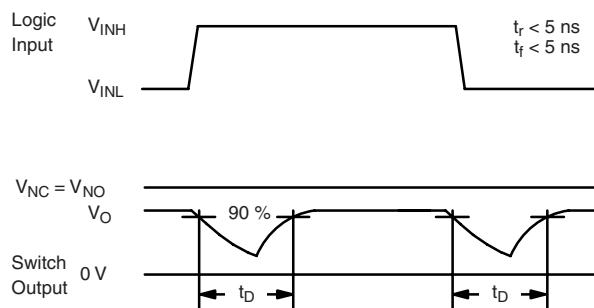
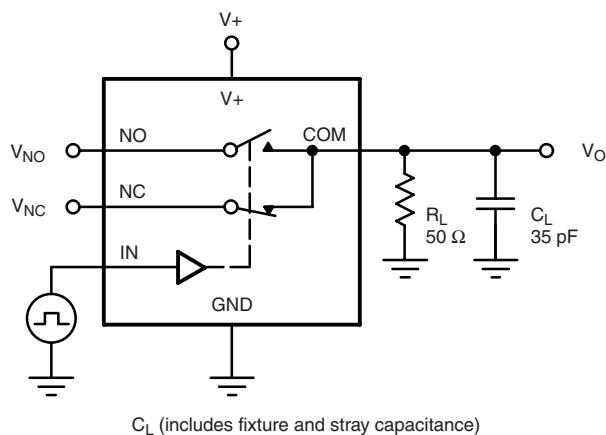
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted


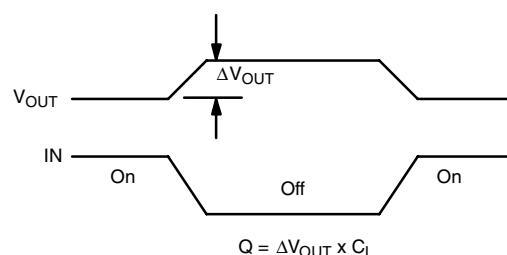
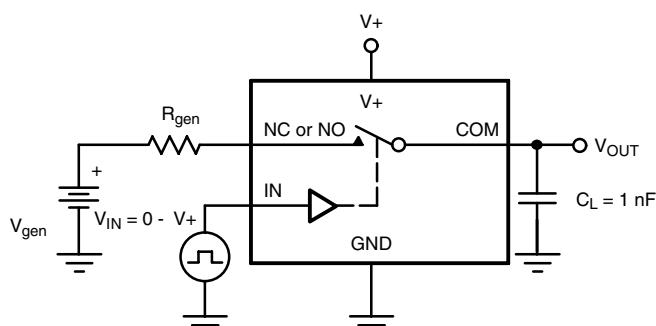
TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted

TEST CIRCUITS


Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

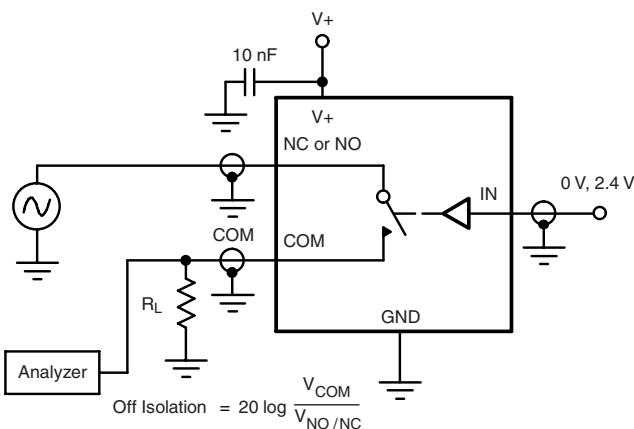
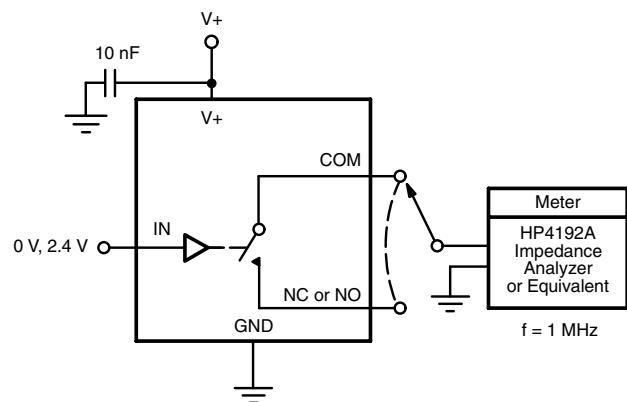
Figure 1. Switching Time


C_L (includes fixture and stray capacitance)

Figure 2. Break-Before-Make Interval


IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

TEST CIRCUITS**Figure 4. Off-Isolation****Figure 5. Channel Off/On Capacitance**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73863>.



Legal Disclaimer Notice

Vishay

Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.